

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC3465

DESCRIPTION

- With TO-3 package
- High voltage
- Fast switching speed

APPLICATIONS

- For switching regulator applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

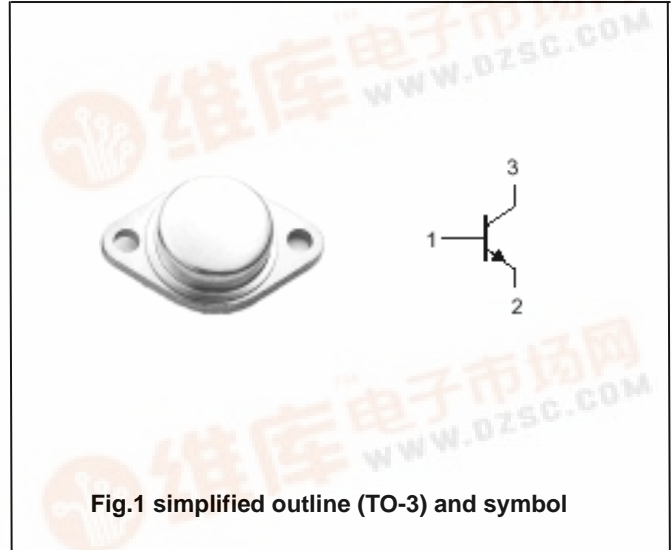


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1100	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		12	A
P _T	Total power dissipation	T _C =25	160	W
T _j	Junction temperature		200	
T _{stg}	Storage temperature		-65~200	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA; R _{BE} =	800			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA; I _E =0;	1100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0;	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A; I _B =1.2A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A; I _B =1.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =0.8A; V _{CE} =5V	10		40	
h _{FE-2}	DC current gain	I _C =4A; V _{CE} =5V	10			
f _T	Transition frequency	I _C =0.8A; V _{CE} =10V		15		MHz
C _{OB}	Collector output capacitance	I _E =0; V _{CB} =10V, f=1MHz		240		pF

◆ h_{FE-1} classifications

K	L	M
10-20	15-30	20-40

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PACKAGE OUTLINE

